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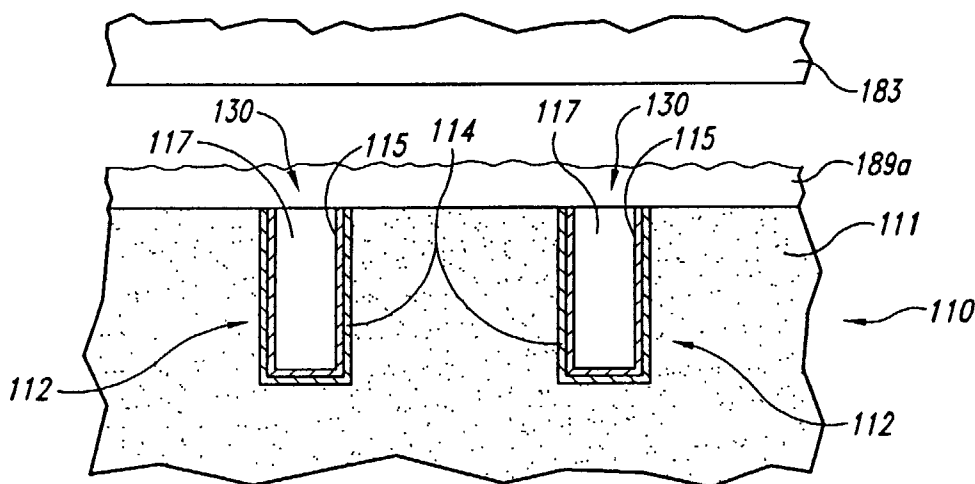
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(54) Title: METHOD AND APPARATUS FOR CHEMICALLY, MECHANICALLY, AND/OR ELECTROLYTICALLY REMOV-
ING MATERIAL FROM MICROELECTRONIC SUBSTRATES



(57) Abstract: Method and apparatus for chemically, mechanically and/or electrolytically removing material from microelectronic substrates. A polishing medium for removing material can include a liquid carrier, an electrolyte disposed in the liquid carrier, and abrasives disposed in the liquid carrier, with the abrasives forming up to about 1% of the polishing liquid by weight. The polishing medium can further include a chelating agent. An electrical current can be selectively applied to the microelectronic substrate via the polishing liquid, and a downforce applied to the microelectronic substrate can be selected based on the level of current applied electrolytically to the microelectronic substrate. The microelectronic substrate can undergo an electrolytic and nonelectrolytic processing on the same polishing pad, or can be moved from one polishing pad to another while being supported by a single substrate carrier.

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